

ABSTRACT

A method for cleaning semiconductor substrates includes a DI water clean operation that uses a spin speed no greater than 350 rpm. The cleaning method may include additional cleaning operations such as an organic clean, an aqueous chemical clean or a DI water/ozone clean. The cleaning method may be used to clean substrates after the conclusion of an etching procedure which exposes a single film between a Cu-containing conductive material and the environment. The spin speed of the DI water clean operation prevents copper corrosion due to breakdown of the film that separates the Cu-containing conductive material from the environment.